

HIGH VOLTAGE NPN POWER TRANSISTOR

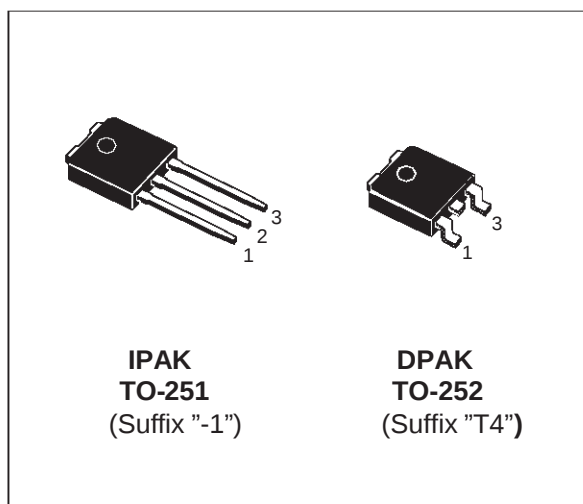
- REVERSE PINS OUT Vs STANDARD IPAK/DPAK PACKAGE
- HIGH VOLTAGE CAPABILITY
- HIGH DC CURRENT GAIN
- THROUGH-HOLE IPAK (TO-251) POWER PACKAGE IN TUBE (SUFFIX "-1")
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")

APPLICATIONS:

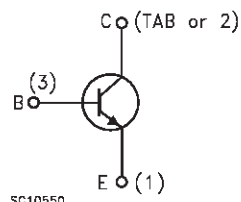
- SWITCH MODE POWER SUPPLIES
- GENERAL PURPOSE SWITCHING

DESCRIPTION

The BUXD87 is manufactured using High Voltage Multi Epitaxial Planar technology for high switching speeds and high voltage withstand capability.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage ($V_{BE} = -1.5V$)	1000	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	450	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5	V
I_C	Collector Current	0.5	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	1	A
I_B	Base Current	0.3	A
I_{BM}	Base Peak Current ($t_p < 5$ ms)	0.6	A
P_{tot}	Total Dissipation at $T_c = 25^\circ C$	20	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ C$
T_j	Max. Operating Junction Temperature	150	$^\circ C$

BUXD87

THERMAL DATA

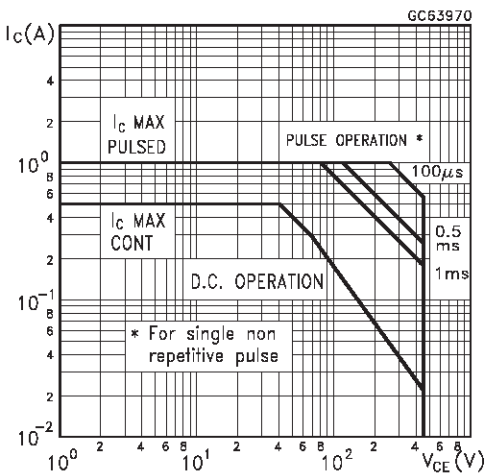
R _{thj-case}	Thermal Resistance Junction-case	Max	6.25	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	100	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

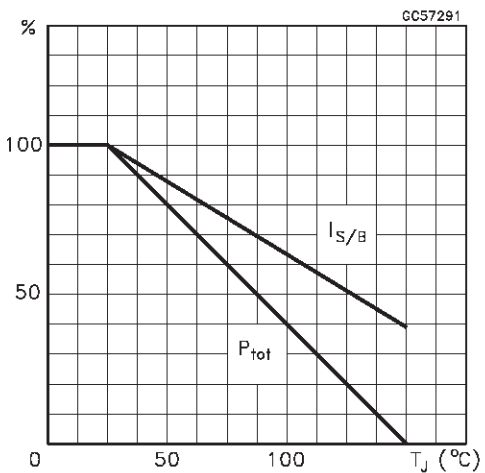
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEV}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = 1000 V V _{CE} = 1000 V T _j = 125 °C			100 1	μA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	I _C = 100 mA	450			V
V _{BEO}	Collector-Base Sustaining Voltage	I _C = 10 mA	5			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 0.1 A I _B = 0.01 A I _C = 0.2 A I _B = 0.02 A			0.8 1	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 0.2 A I _B = 0.02 A			1	V
h _{FE} *	DC Current Gain	I _C = 50 mA V _{CE} = 5 V I _C = 40 mA V _{CE} = 5 V	12	50		
f _T	Transition Frequency	I _C = 50 mA V _{CE} = 10 V f=1MHz		20		MHz
t _s t _f	RESISTIVE LOAD Storage Time Fall Time	V _{CC} = 250 V I _C = 200 mA I _{B1} = 40 mA I _{B2} = -80 mA t _p = 20 μs		4.5 0.5		μs μs

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

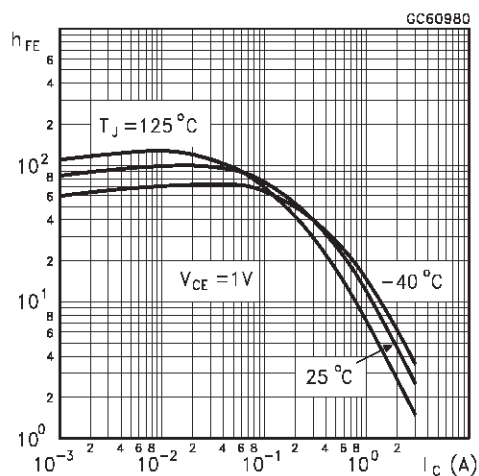
Safe Operating Area



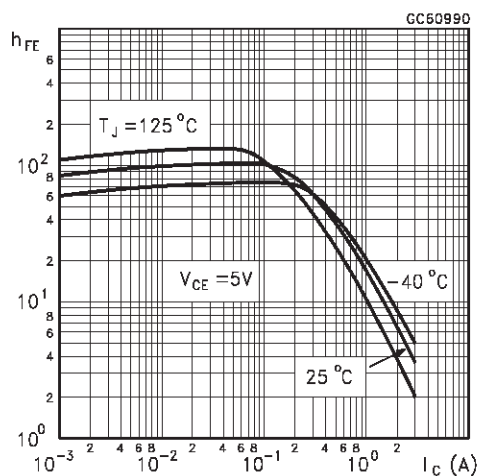
Derating Curves



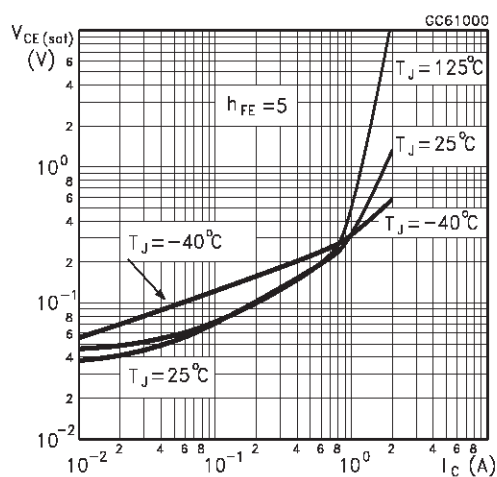
DC Current Gain



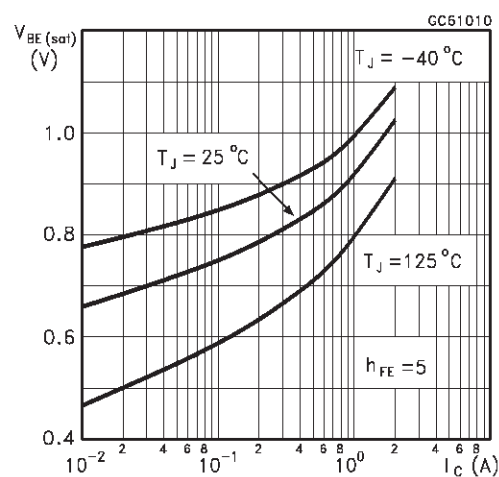
DC Current Gain



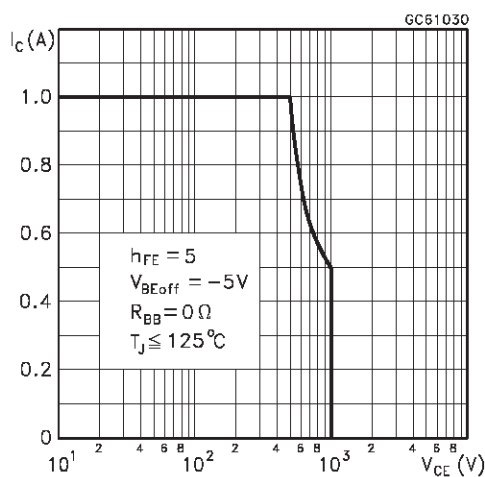
Collector Emitter Saturation Voltage



Base Emitter Saturation Voltage

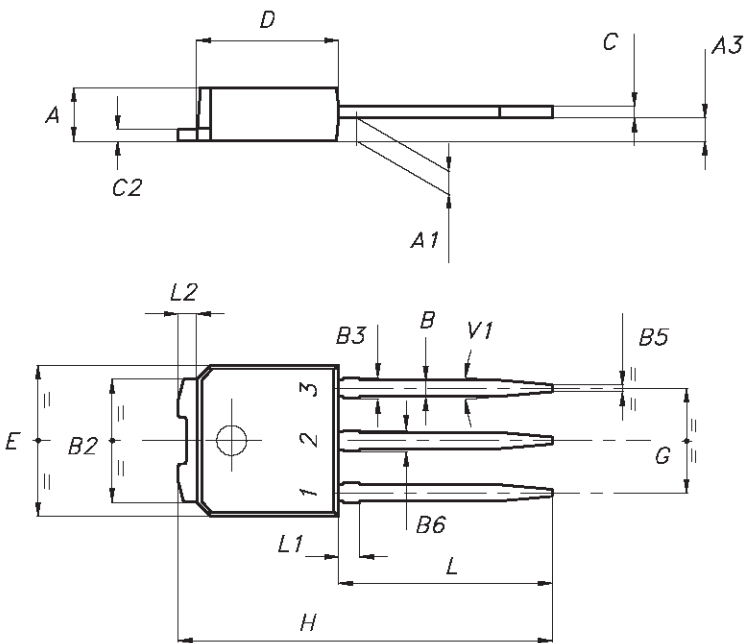


Reverse Biased SOA



TO-251 (IPAK) MECHANICAL DATA

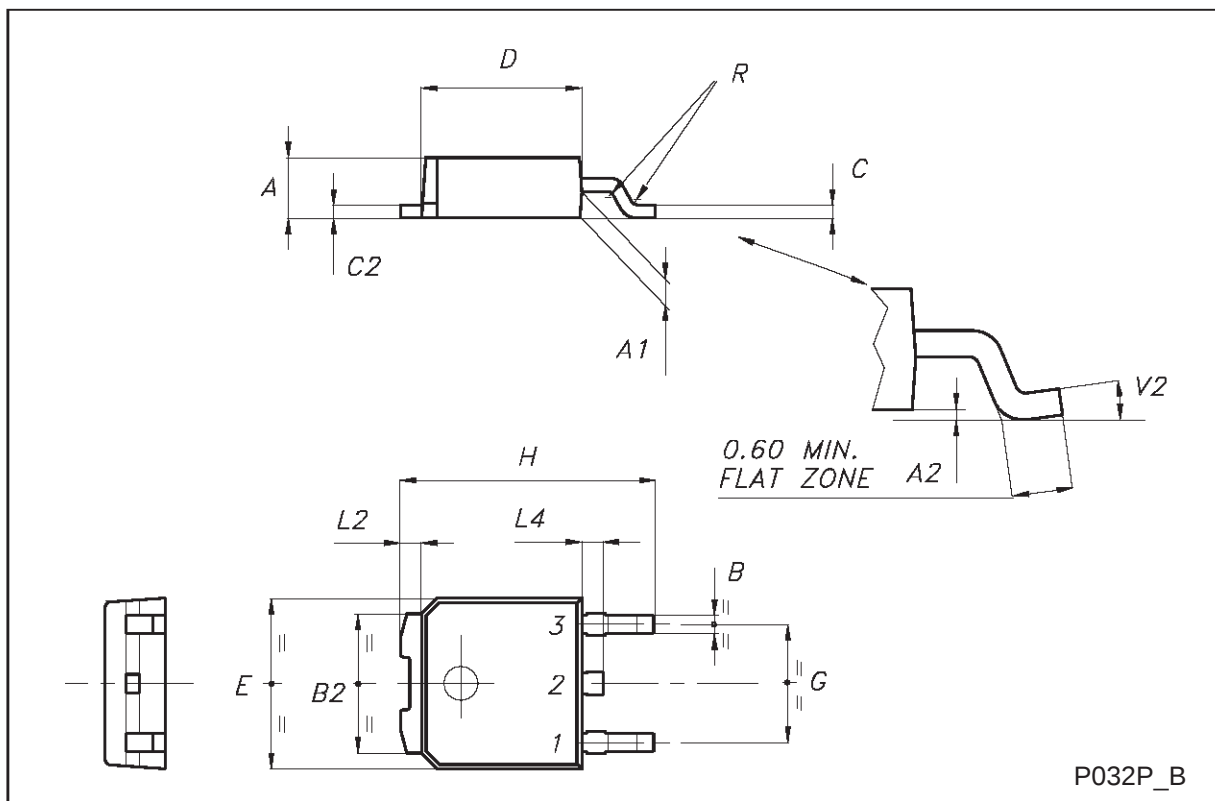
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A3	0.70		1.30	0.028		0.051
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
B3			0.85			0.033
B5		0.30			0.012	
B6			0.95			0.037
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.237		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	15.90		16.30	0.626		0.642
L	9.00		9.40	0.354		0.370
L1	0.80		1.20	0.031		0.047
L2		0.80	1.00		0.031	0.039
V1		10°			10°	



P032N_E

TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



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